SCT51240

Rev 1.6

- Wide Supply Voltage Range: 4.5V - 24V
- 4A Peak Source Current and 4A Peak Sink Current
- Dual Input Configuration: Non-Inverting (IN+) or Inverting (IN-) Input
- Negative Input Voltage Capability: Down to -5V
- TTL Input-Logic Threshold
- Propagation Delay: 12ns
- Fast Rising and Falling Time: 9ns and 6ns
- Low Quiescent Current: 38uA
- Under Voltage Lock Out Protection of Supply Voltage
- Output Low When Input Floating
- Thermal Shutdown Protection: 170°C
- Available in TSOT23-5L Package

- Power MOSFET Gate Driver
- IGBT Gate Driver
- GaN Device Gate Driver
- Switching Power Supply
- Motor Control, Solar Power

The SCT51240 is a wide supply, single channel, high speed, low side gate driver for power MOSFET, IGBT, and wide band-gap device such as GaN. The 24V power supply rail enhances the driver output ringing endurance during the power device transition. The capability to switch below 5V power supply makes the SCT51240 work well for the low voltage threshold power device.

The SCT51240 can source and sink 4A peak current along with rail-to-rail output driving capability. The minimum 12ns input to output propagation delay enables it suitable for high frequency power converter application. The SCT51240 features wide input hysteresis that is compatible for TTL low voltage logic. The SCT51240 has the capability to handle negative input down to -5V, which enhances the input noise immunity. The IN+ and IN- input provides the flexibility to configure the SCT51240 either as non-inverting or inverting driver.

The SCT51240 has very low quiescent current that reduces the stand by power loss in the power converter. The SCT51240 gate driver adopts non-overlap driver design to avoid the shoot-through of output stage.

The SCT51240

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Revision 1.0: Released to Production.

Revision 1.3: Page 8 Table 1, Page 9 input stage description

Revision 1.4: Add high limit for I_Q and RO in EC table

Revision 1.5: Correct pin number in function block diagram

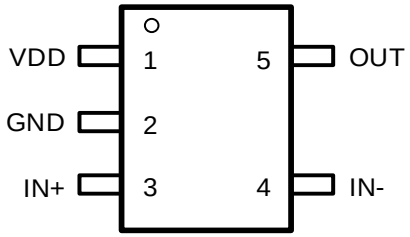
Revision 1.6: Update DEVICE ORDER INFORMATION

ORDERABLE DEVICE	PACKAGING TYPE	STANDARD PACK QTY	PACKAGE MARKING	PINS	PACKAGE DESCRIPTION
SCT51240TWBR	Tape & Reel	3000	1240	5	TSOT23-5L

Over operating free-air temperature unless otherwise noted(1)

DESCRIPTION	MIN	MAX	UNIT
IN+, IN-	-5	26	V
OUT	-0.3	26	V
VDD	-0.3	26	V
Operating junction temperature T_J (2)	-40	150	°C
Storage temperature T_{STG}	-65	150	°C

Top View: TSOT23-5pin Plastic



(1) Stresses beyond those listed under Absolut Maximum Rating may cause device permanent damage. The device is not guaranteed to function outside of its Recommended Operation Conditions.

(2) The IC includes over temperature protection to protect the device during overload conditions. Junction temperature will exceed 150°C when over temperature protection is active. Continuous operation above the specified maximum operating junction temperature will reduce lifetime.

NAME	NO.	PIN FUNCTION
VDD	1	Power supply of gate driver, must be decoupled by ceramic cap. A 0.1uF, and 1uF or 10uF are recommended.
GND	2	Power ground. Must be soldered directly to ground planes for improved thermal performance and electrical contact.
IN+	3	Non-inverting logic input, TTL compatible. Floating logic low. In Non-Inverting configuration, apply PWM signal on IN+. In inverting configuration, connect IN+ to VDD.
IN-	4	Inverting logic input, TTL compatible. Floating logic low. In Non-Inverting configuration, connect IN- to GND. In inverting configuration, apply PWM signal on IN-.
OUT	5	Gate driver output.

Over operating free-air temperature range unless otherwise noted

PARAMETER	DEFINITION	MIN	MAX	UNIT
V_{DD}	Supply voltage range	4.5	24	V
$V_{IN+,IN-}$	Input voltage range	-5	24	V
T_J	Operating junction temperature	-40	150	°C

PARAMETER	DEFINITION	MIN

V_{DD}=12V, T_J=-40°C~125°C, typical values are tested under 25°C.

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
Power Supply and Output						
V_{DD}	Operating supply voltage		4.5		24	V
V_{DD_UVLO}	Input UVLO Hysteresis	V_{DD} rising		4.2 300	4.5	V mV
I_Q	Quiescent current	IN+=IN-=GND or IN+=IN-=VDD, VDD=3.5V, T_J=25°C		38	50	uA
		IN+=IN-=GND or IN+=IN-=VDD, VDD=3.5V, T_J=-40°C~125°C		38	65	uA
		IN+=IN-=GND, V_{DD}=12V		120	190	uA
INPUTS						
V_{IN+}	Input+ logic high threshold			2.1	2.4	V
V_{IN+}	Input+ logic low threshold		0.8	1.0		V
V_{IN+_Hys}	Hysteresis			1.1		V
V_{IN-_H}	Input- logic high threshold			2.1	2.4	V
V_{IN-_L}	Input- logic low threshold		0.8	1.0		V
V_{IN-_Hys}	Hysteresis			1.1		V
OUTPUTS						
V_{DD_VOH}	Output High Voltage (only PMOS ON)	I_{OUT}=10mA			150	mV
V_{OL}	Output Low Voltage	I_{OUT}=10mA			10	mV
$I_{SINK/SRC}$	Output Sink/Source peak current	C_{Load}=10nF, F_{sw}=1kHz		4		A
R_{OH}	Output pull high resistance (only PMOS ON)	I_{OUT}= -10mA		8.5	17	
R_{OL}	Output pull low resistance	I_{OUT}= 10mA		0.6	1.2	
Timing						
T_R	Output rising time	C_{Load}=1nF		9	20	ns
T_F	Output falling time	C_{Load}=1nF		6	20	ns
T_{D_IN+}	IN+ to output propagation delay, Rising edge			12	25	ns
	IN+ to output propagation delay, Falling edge			12	25	ns
T_{D_IN-}	IN- to output propagation delay, Rising			12	25	ns
	IN- to output propagation delay, Falling			12	25	ns
T_{MIN_ON}	Minimum input pulse width	C_{Load}=1nF		20	30	ns
Protection						
T_{SD}	Thermal shutdown threshold	T_J rising		170		°C
	Hysteresis			25		°C

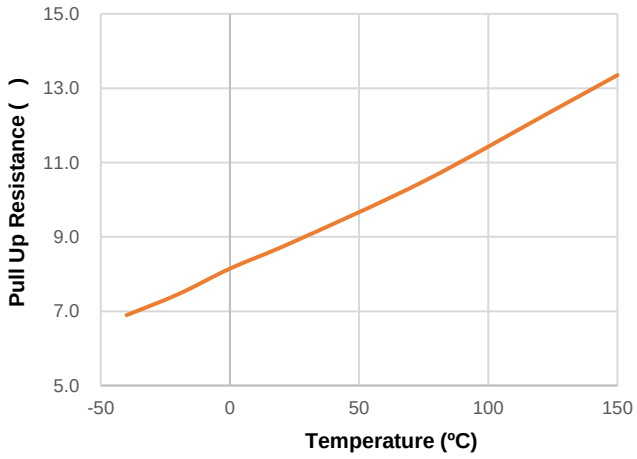


Figure 7. ROH vs Temperature

Figure 8. ROL Vs Frequency

For more information

Overview

The SCT51240 is a up to 24V wide supply, single channel, high speed, low side gate driver for power MOSFET and IGBT. The SCT51240 can source and sink 4A peak current along with the minimum propagation delay 12ns from input to output. The ability to handle -5V DC input increases the driver input stage noise immunity, the 24V rail-to-rail output improves the SCT51240 output stage robustness during the switching load fast transition.

The SCT51240 features a dual-input design by implementing both inverting (IN pin) and non-inverting (IN+ pin) configuration in the same device. Either the IN+ or IN pin can be used to control the state of the driver output. The internal pull-up or pull-down resistors on the input pins ensure that output is held low when the input pins are in floating condition. As a result, the unused input pin must be biased properly to ensure that driver output is enabled for normal operation. Table 1 is the device logic truth table.

Table 1: the SCT51240 Device Logic.

IN+	IN-	OUT
L	L	L
L	H	L
H	L	H
H	H	L
Floating	Any	L
Any	Floating	L

VDD Power Supply

The SCT51240 operates under a supply voltage range between 4.5V to 24V. For the best high-speed circuit performance, two VDD bypass capacitors in parallel are recommended to prevent noise problems on supply VDD. A 0.1- F surface mount ceramic capacitor must be located as close as possible to the VDD to GND pins of the SCT51240. In addition, a larger capacitor (such as 1 F or 10uF) with relatively low ESR must be connected in parallel, in order to help avoid the unexpected VDD supply glitch. The parallel combination of capacitors presents a low impedance characteristic for the expected current levels and switching frequencies in the application.

Under Voltage Lock Out (UVLO)

The SCT51240 Under Voltage Lock Out (UVLO) rising threshold is typically 4.2 V with 300-mV typical hysteresis.

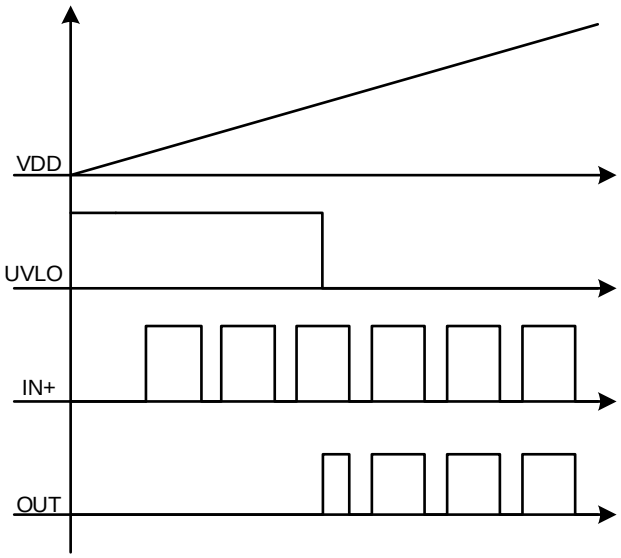


Figure 9. SCT51240 Output Vs VDD

Input Stage

The input of SCT51240 is compatible on TTL logic that is independent of the VDD supply voltage. With typically high threshold = 2.1 V and typically low threshold = 1.0 V, the logic level thresholds are conveniently driven by PWM control signals derived from 3.3-V and 5-V digital power-controller devices. Wider hysteresis offers enhanced noise immunity compared to traditional TTL logic implementation, where the hysteresis is typically less than 0.5 V. SCT51240 also features tight control of the input threshold voltage that ensures stable operation across temperature. The low input capacitance on the input pins increases switching speed and reduces the propagation delay.

The SCT51240 features a dual-input configuration with two input pins available to control the state of the output. The user has the flexibility to configure the device by using either a non-inverting input pin (IN+) or an inverting input pin (IN). The state of the output pin depends on the bias on both the IN+ and IN pins. Refer to the input/output logic truth table (Table 1) and the Typical Application Diagrams Figure 11. When any of the input pin is in a floating condition, the driver output is held low state to guarantee the system robustness. There is a 500kOhm ground pull-down resistor on IN+ pin and a 400kOhm VDD pull-up resistor on IN- pin. To achieve the proper output, the IN+ and IN- pin must be properly biased.

1. To configure the SCT51240 as a non-inverting driver, apply the PWM input signal on IN+ pin and bias the IN- pin with ground, where the IN- pin can be used as an enable pin with low effective.
2. To configure the SCT51240 as an inverting driver, apply the PWM input signal on IN- pin and bias the IN+ pin with VDD, where the IN+ can be used as an enable pin with high effective.

Output Stage

The SCT51240 output stage features the pull up structure with P-type MOSFET PM1 and N-type MOSFET NM1 in parallel, as shown in Figure 10. PM1 provides the pull up capability when OUT approaches VDD and the NM1 holds off state, which guarantees the driver output is up to VDD rail. The measurable on-resistance R_{OH} in steady state is the conduction resistance of PM1. NM1 provides a narrow instant peak sourcing current up to 4A to eliminate the turn on time and delay. During the output turn on transition, the equivalent hybrid pull on transient resistance is $1.5xR_{OL}$, which is much lower than the R_{OH}.

The N-type MOSFET NM2 composes the output stage pull down structure; the R_{OL} is the DC measurement and represents the pull down impedance. The output stage of SCT51240 provides rail-to-rail operation, and is able to supply 4A sourcing and 4A sinking current. The presence of the MOSFET-body diodes also offers low impedance path to damp overshoots and undershoots. The outputs of the dual channel drivers are designed to withstand 500-

mA reverse current without either damaging the device or causing the logic malfunction.

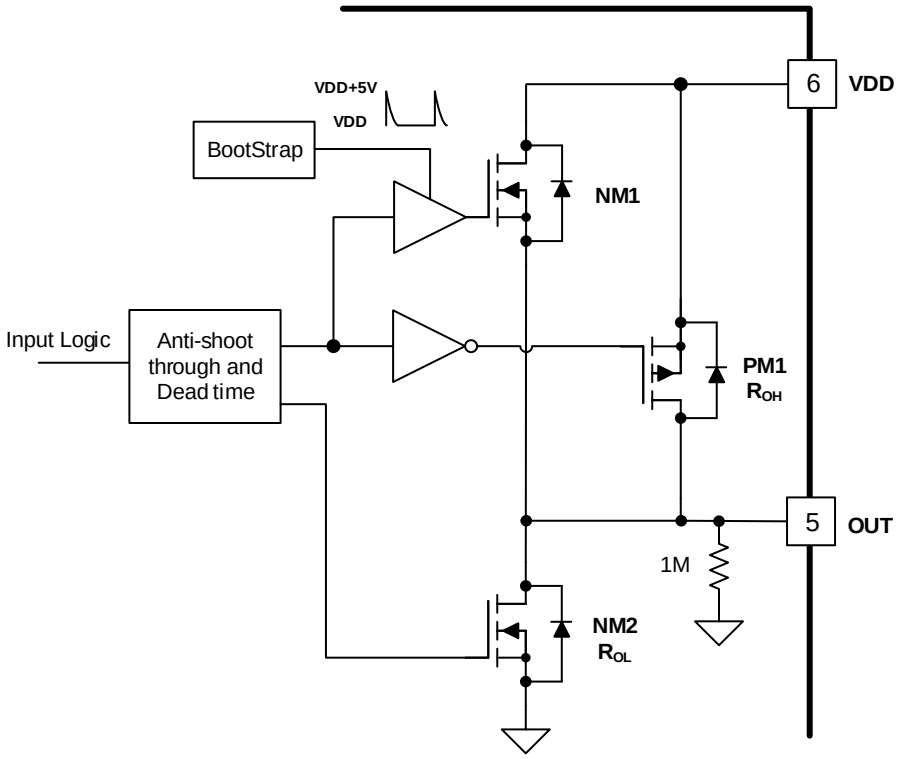


Figure 10. SCT51240 Output Stage

Thermal Shutdown

Once the junction temperature in the SCT51240 exceeds 170° C, the thermal sensing circuit stops switching until the junction temperature falling below 145° C, and the device restarts. Thermal shutdown prevents the damage on device during excessive heat and power dissipation condition.

Typical Application

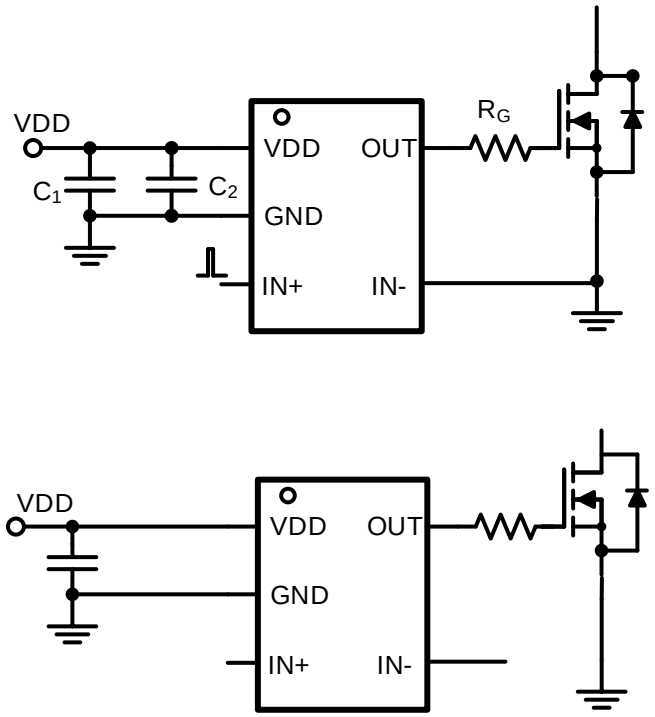


Figure 11. Single Channel Driver Non-Inverting and Inverting Application

Driver Power Dissipation

Generally, the power dissipated in the SCT51240 depends on the gate charge required of the power device (Qg), Switching frequency, and use of external gate resistors. The SCT51240 features very low quiescent currents and internal logic to eliminate any shoot-through in the output driver stage, their effect on the power dissipation within the gate driver is negligible.

For the pure capacitive load, the power loss of SCT51240 is:

(1)

Where

- V_{DD} is supply voltage
- C_{Load} is the output capacitance
- f_{SW} is the switching frequency

For the switching load of power MOSFET, the power loss of the driver is shown in equation (1), where charging a capacitor is determined by using the equivalence $Q_g = C_{LOAD}V_{DD}$. The gate charge includes the effect of the input capacitance plus the added charge needed to swing the drain voltage of the power device as it switches between the ON and OFF states. Manufacturers provide specifications with the typical and maximum gate charge, in nC, to switch the device under specified conditions.

(2)

Where

- Q_g is the gate charge of the power device
- f_{SW} is the switching frequency[X]

Where

Layout Guideline

The SCT51240 provides the 4A output driving current and features very short rising and falling time at the power devices gate. The high di/dt causes driver output unexpected ringing when the driver output loop is not optimized. The regulator could suffer from malfunction and EMI noise if the power device gate has serious ringing. Below are the layout recommendations with using SCT51240 and Figure 16 is the layout example.

Put the SCT51240 as close as possible to the power device and minimize the gate driving loop including the driver output and power device gate. The power supply decoupling capacitors needs to be close to the VDD pin and GND pin to reduce the supply ripple.

Star-point grounding is recommended to minimize noise coupling from one current loop to the other. The GND of the driver connects to the other circuit node such as source of power MOSFET or ground of PWM controller at single point. The connected paths must be as short as possible to reduce parasitic inductance. A ground plane provides noise shielding and thermal dissipation as well.

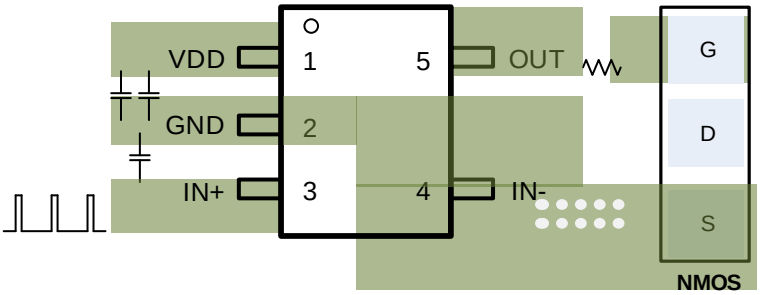


Figure 16. SCT51240 PCB Layout Example

Thermal Considerations

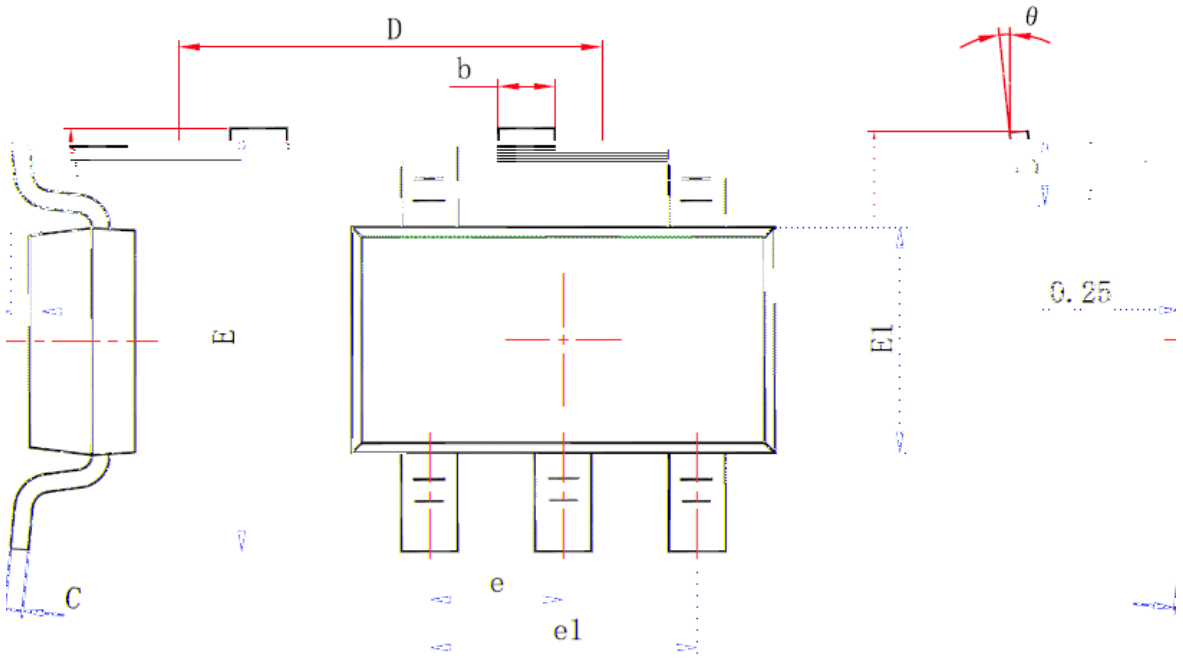
The maximum IC junction temperature should be restricted to 170°C under normal operating conditions. Calculate the maximum allowable dissipation, $P_{D(max)}$, and keep the actual power dissipation less than or equal to $P_{D(max)}$. The maximum-power-dissipation limit is determined using Equation (4).

(4)

where

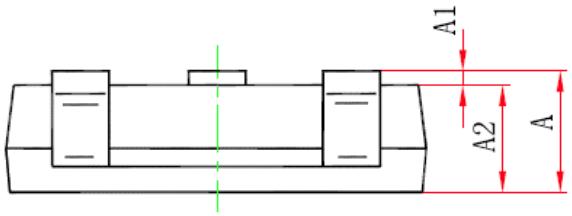
- T_A is the maximum ambient temperature for the application.
- R is the junction-to-ambient thermal resistance given in the Thermal Information table.

The real junction-to-ambient thermal resistance R of the package greatly depends on the PCB type, layout, and environmental factor. Soldering the ground pin to a large ground plate enhance the thermal performance. Using more vias connects the ground plate on the top layer and bottom layer around the IC without solder mask also improves the thermal capability.



TOP VIEW

BOTTOM VIEW

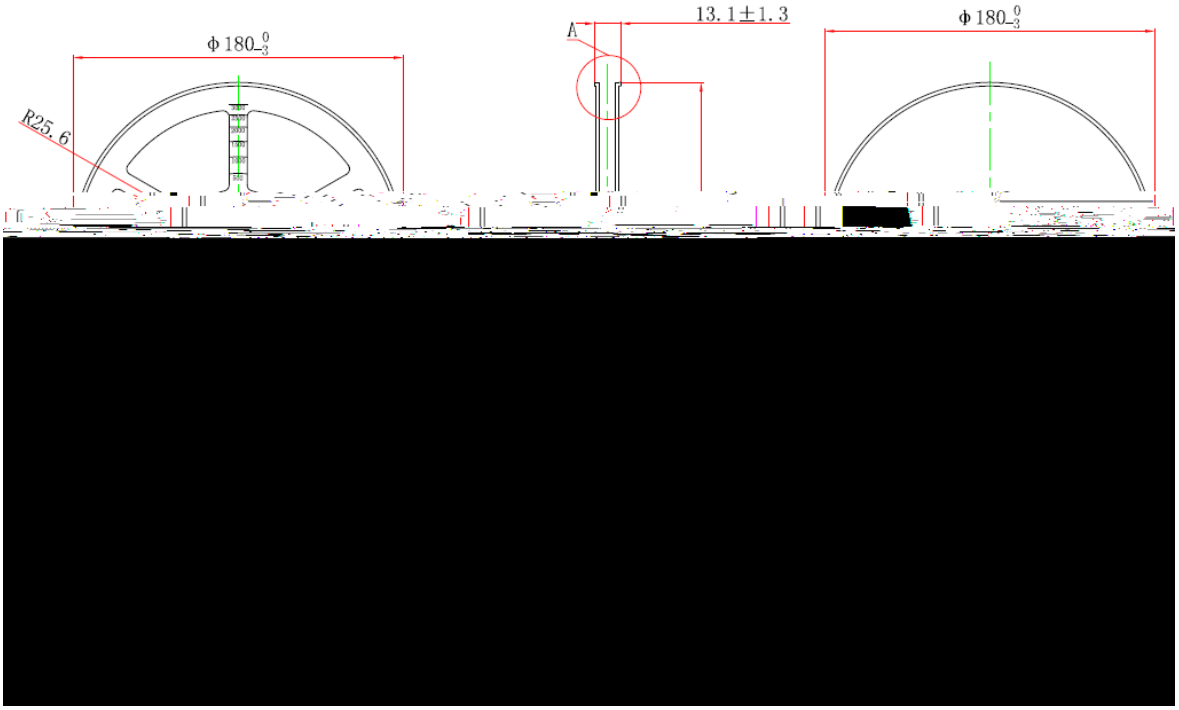


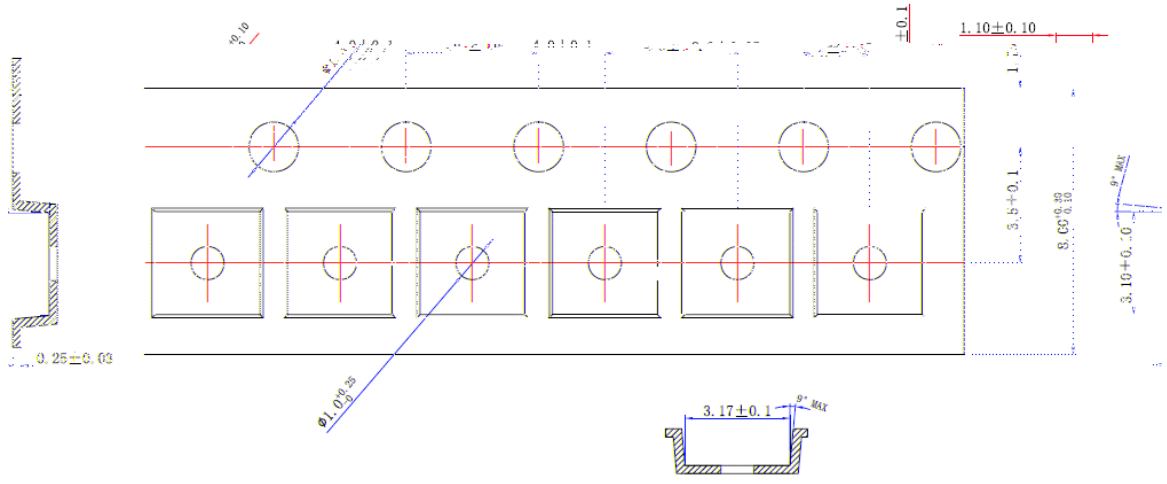
SIDE VIEW

SYMBOL	Unit: Millimeter		
	MIN	TYP	MAX
A	---	---	0.9
A1	0.02	---	0.09
A2	0.7	---	0.8
b	0.35	---	0.5
c	0.08	---	0.2
D	2.82		3.02
E	2.65		2.95
E1	1.6		1.7
e	0.95 (BSC)		
e1	1.90 (BSC)		
L	0.3		0.6
	0°		8°

NOTE:

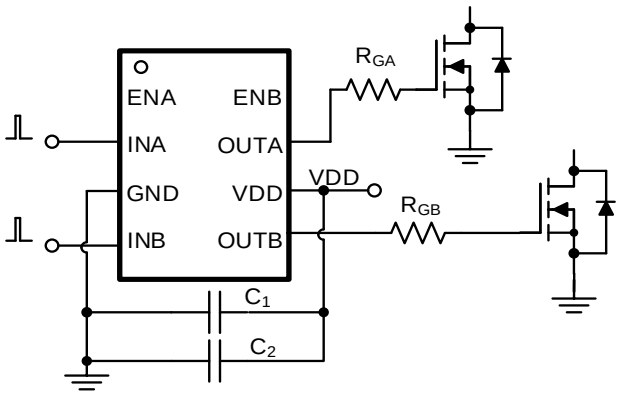
1. Drawing proposed to be made a JEDEC package outline MO-220 variation.
2. Drawing not to scale.
3. All linear dimensions are in millimeters.
4. Thermal pad shall be soldered on the board.
5. Dimensions of exposed pad on bottom of package do not include mold flash.
6. Contact PCB board fabrication for minimum solder mask web tolerances between the pins.





Feeding Direction

SCT52240 Typical Application



PART NUMBERS	DESCRIPTION	COMMENTS
SCT52240	Up to 24V Supply, 4-A Dual Channel High Speed Low Side Driver	• Stackable Output Application • -5V Input Capability

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